

Applications

- IEEE802.16e WiMAX™
- Mobile WiMAX datacards, modules and terminals

Features

- 2.3-2.7 GHz operation
- 25 dBm Linear output power, at 3.3V
- 37 dB gain
- Integrated Step Attenuator and output power detector
- All RF ports matched for 50 Ω operation
- Supply voltage: 2.9 V – 4.2 V
- Lead free, Halogen free, ROHS compliant package (4 mm x 4 mm x 0.9 mm), MSL 1

Product Description

The SE7265L WiMAX Power Amplifier is a high performance device offering high output power with high linearity and exceptional efficiency. Designed for portable or mobile applications in the 2.3-2.7 GHz band, it supports the IEEE 802.16e wireless standards.

Ordering Information

Part No.	Package	Remark
SE7265L	16 pin QFN	Samples
SE7265L-R	16 pin QFN	Tape and Reel
SE7265L-EK1	N/A	Evaluation kit

Functional Block Diagram

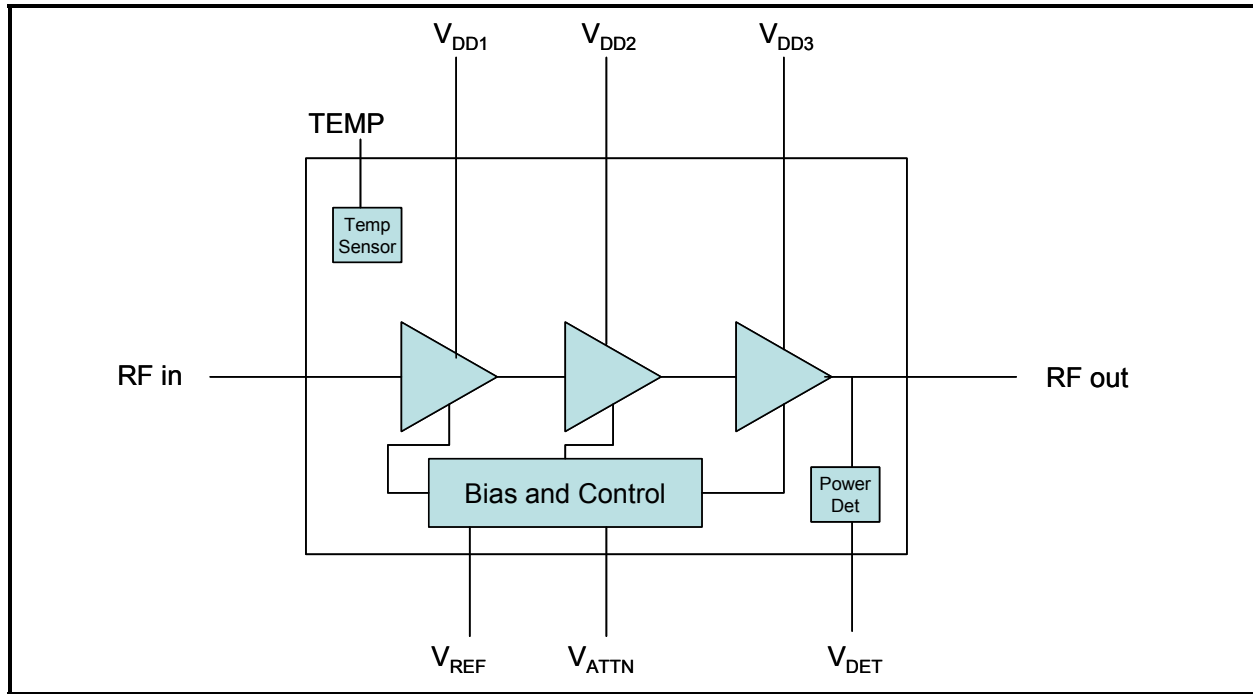


Figure 1: Functional Block Diagram

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Product Preview

The datasheet contains information from the product concept specification. SiGe Semiconductor, Inc. reserves the right to change information at any time without notification.

Preliminary Information

The datasheet contains information from the design target specification. SiGe Semiconductor, Inc. reserves the right to change information at any time without notification.

Production testing may not include testing of all parameters.

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